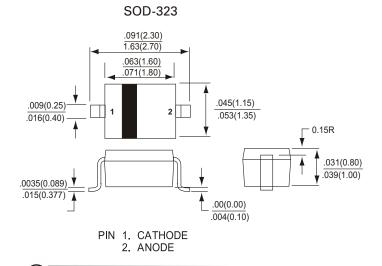
# SD103AWS/SD103BWS/SD103CWS

## SURFACE MOUNT SCHOTTKY BARRIER DIODES

#### SMALL SIGNAL SCHOTTKY DIODES 350m AMPERES 20~40 VOLTS







 $(\Rightarrow)$ 

Low Forward Voltage

Very Small Conduction Losses

Schottky Barrier Diodes Encapsulated in SOD-323 Package

MAXIMUM RATING (TA=25°C unless otherwise noted)

MECHANICAL DATA

Polarity : Cathode Band Leads : Solderable per MIL-STD-202 Method 208 Wigth : 0.004grams (approx)

CHARACTERISTICS	SYMBOL	SD103AWS	SD103BWS	SD103CWS	UNITS
Peak Repetitive Reverse Voltage	Vrrm				
Working Peak Reverse Voltage	VRWM	40	30	20	Volts
DC Blocking Voltage	VR				
RMS Reverse Voltage	VR(RMS)	28	21	14	Volts
Average Repetitive Output Current	IFAV	350			mA
Non-Repetitive Peak Forward Surge Current @ t≦1.0S	IFSM	1.5			А
Power Dissipation (1)	PD	200			mW
Typical thermal Resistance junction to Ambient Note <sup>(1)</sup>	R $ heta$ ja	625			°C / W
Operating & Storage Temperature Range	Tj Tstg		°C		

#### ELECTRICAL CHARACTERISTICS (TA=25°C unless otherwise noted)

CHARACTERISTICS	SYMBOL	Min	Тур	Max	UNITS
Reverse Breakdown Voltage <sup>(2)</sup> SD103AWS (I <sub>R</sub> = 100uA) SD103BWS SD103CWS	V(BR)R	40 30 20	-	-	Volts
Forward Voltage Note <sup>(2)</sup> IF = 20mA IF = 200mA	VF	-	-	0.37 0.60	Volts
Reverse Current Note $^{(2)}$ V_R = 30V, SD103AWS V_R = 32V, SD103BWS V_R = 10V, SD103CWS	IR	-	-	5.0	μ Amps
Junction Capacitance, $f = 1 MHz$ , $V_R = 0 VDC$	CJ	-	50	-	pF
$\label{eq:Reverse Recovery Time} \begin{array}{l} I_F = I_F = 200 mA, \\ I_{RR} = 0.1^*  I_R,  R_L = 100 \Omega \end{array}$	Trr	-	10	-	nS

NOTES :

1. Valid provited that leads are kept at ambient tememperature.

2. Pulse Test: Pulse width=300µs, Duty Cycle≦2%



## SD103AWS/SD103BWS/SD103CWS

### SURFACE MOUNT SCHOTTKY BARRIER DIODES

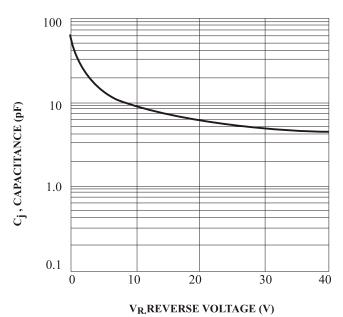


FIG. 2 Typ, Junction Capacitance vs. Reverse Voltage

